

23. The [method] structure of claim 19, wherein the strain energy of said antireflective compound is at least than about 10 kcal/mol.

24. The [method] structure of claim 19, wherein said substrate comprises a silicon wafer.

25. The [method] structure of claim 19, wherein the antireflective compound layer on said substrate surface has a thickness of from about 300-5000 Å.

26. The [method] structure of claim 19, wherein said antireflective compound layer is substantially insoluble in solvents utilized in said photoresist layer.

27. The [method] structure of claim 19, wherein the antireflective compound layer absorbs at least about 90% of light at a wavelength of from about 150-500 nm.

28. The [method] structure of claim 19, wherein the antireflective compound layer, when subjected to light of a predetermined wavelength, has a k value of at least about 0.1 at said predetermined wavelength.

29. The [method] structure of claim 19, wherein the antireflective compound layer has a percent conformality of at least about 85%.